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WE CLAIM:

1. Apparatus for processing data, said apparatus comprising:

at least one memory having a plurality of memory storage locations associated with respective memory addresses; and

a self-test controller operable to control self-test of said at least one memory; wherein

said self-test controller is responsive to a self-test instruction to perform at least one memory access to each memory location within a sequence of memory storage locations, memory address changes between successive memory locations accessed within said sequence of memory storage locations being selected in dependence upon said self-test instruction such that said self-test controller may be configured by said self-test instruction to implement different memory test methodologies.

- 2. Apparatus as claimed in claim 1, wherein said self-test controller is operable to execute a plurality of self-test instructions to perform a sequence of memory tests, said self-test instructions being programmable to allow different sequences of memory tests to be specified by different users.
- 3. Apparatus as claimed in claim 2, wherein said sequence of memory tests may be changed to match different memories.
- 4. Apparatus as claimed in claim 2, wherein said sequence of memory tests may be changed to match different fabrication characteristics and test needs.
 - 5. Apparatus as claimed in claim 1, wherein said memory addresses are physical row and column addresses within said at least one memory.

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- 6. Apparatus as claimed in claim 1, wherein said self-test instruction specifies data to be written to said memory as part of said at least one memory access.
- 7. Apparatus as claimed in claim 1, wherein said memory address changes between successive memory locations as selected in dependence upon said self-test instruction and said self-test controller allow one or more of the following memory test operations to be performed:
- (i) write specified data to all memory locations within a range of memory addresses;
 - (ii) read data from all memory locations within a range of memory addresses;
- (iii) write specified data to memory locations having a checkerboard pattern of memory addresses;
- (iv) read data from memory locations having a checkerboard pattern of memory addresses;
 - (v) conduct a march C memory test;
- (vi) read data from and write specified data to a sequence of memory locations within a memory arranged in rows and columns of memory locations such that memory locations within a row of memory locations are accessed in turn before a next row of memory locations is selected for access;
- (vii) read data from and write specified data to a sequence of memory locations within a memory arranged in rows and columns of memory locations such that memory locations within a column of memory locations are accessed in turn before a next column of memory locations is selected for access;
- (viii) read data from, write specified data to and read data from a sequence of memory locations within a memory arranged in rows and columns of memory locations such that memory locations within a row of memory locations are accessed in turn before a next row of memory locations is selected for access;
- (ix) read data from, write specified data to and read data from to a sequence of memory locations within a memory arranged in rows and columns of memory

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locations such that memory locations within a column of memory locations are accessed in turn before a next column of memory locations is selected for access;

- (x) for a sequence of memory locations, repeatedly write a value to one or more bitlines within said memory and then read a complementary value stored within a memory location sharing said one or more bitlines; and
- (xi) for a sequence of memory locations, repeatedly read a value from a memory location while interjecting opposing data writes;
- (xii) a predetermined combination of memory test operations as defined in (i) to (xi) for go/nogo testing where manufacture's test methods do not have specific requirements; and
- (xiii) creating false read data at specific points in order to validate fail detection.
- 8. Apparatus as claimed in claim 1, further comprising a processor core, said processor core, said at least one memory and said self-test controller being formed together on an integrated circuit.
- 9. Apparatus as claimed in claim 1, wherein said at least one memory is one of a synthesized memory and a custom memory.
- 10. Apparatus as claimed in claim 1, wherein an interface circuit is disposed between said self-test controller and said at least one memory, said interface circuit serving to adapted values and timings of signals passed between said self-test controller and said at least one memory to accommodate differing value and timing properties of said at least one memory.
- 11. Apparatus as claimed in claim 10, wherein said interface circuit maps a memory address value generated by said self-test controller to a logical address value to be input to said at least one memory.

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- 12. Apparatus as claimed in claim 1, comprising a plurality of memories and said self-test instruction specifies to which of said plurality of memories said self-test instruction is to be applied.
- 5 13. Apparatus as claimed in claim 1, wherein said self-test instruction specifies in which of a plurality of different ways a detected memory error is to be reported by said self-test controller.
 - 14. Apparatus as claimed in claim 10, wherein said interface circuit includes a result data register in which result data from testing said at least one memory may be captured and said self-test controller is responsive to a self-test instruction to read result data from said result data register.
 - 15. Apparatus as claimed in claim 1, wherein said self-test instruction specifies a size of said at least one memory to be tested.
 - 16. Apparatus as claimed in claim 1, wherein said self-test instruction is serially loaded into said self-test controller.
- 20 17. Apparatus as claimed in claim 1, wherein said at least one memory and said self-test controller are formed together on an integrated circuit having a plurality of external signal pins, said self-test controller having one or more external signal pins through which one or more self-test instructions may be applied to said self-test controller.
 - 18. A method of testing a memory having a plurality of memory storage locations associated with respective memory addresses, said method comprising the steps of:

passing a self-test instruction to a self-test controller coupled to said memory; and

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in response to said self-test instruction, performing at least one memory access to each memory location within a sequence of memory storage locations, memory address changes between successive memory locations accessed within said sequence of memory storage locations being selected in dependence upon said self-test instruction such that said self-test controller may be configured by said self-test instruction to implement different memory test methodologies.

- 19. A method as claimed in claim 18, comprising executing a plurality of self-test instructions with said self-test controller to perform a sequence of memory tests, said self-test instructions being programmable to allow different sequences of memory tests to be specified by different users.
- 20. A method as claimed in claim 19, wherein said sequence of memory tests may be changed to match different memories.
- 21. A method as claimed in claim 19, wherein said sequence of memory tests may be changed to match different fabrication characteristics and test needs.
- 22. A method as claimed in claim 18, wherein said memory addresses are physical row and column addresses within said at least one memory.
 - 23. A method as claimed in claim 1, wherein said self-test instruction specifies data to be written to said memory as part of said at least one memory access.
- 24. A method as claimed in claim 1, wherein said memory address changes between successive memory locations as selected in dependence upon said self-test instruction and said self-test controller allow one or more of the following memory test operations to be performed:
- (i) write specified data to all memory locations within a range of memory
 addresses;

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- (ii) read data from all memory locations within a range of memory addresses;
- (iii) write specified data to memory locations having a checkerboard pattern of memory addresses;
- (iv) read data from memory locations having a checkerboard pattern of memory addresses;
 - (v) conduct a march C memory test;
 - (vi) read data from and write specified data to a sequence of memory locations within a memory arranged in rows and columns of memory locations such that memory locations within a row of memory locations are accessed in turn before a next row of memory locations is selected for access;
 - (vii) read data from and write specified data to a sequence of memory locations within a memory arranged in rows and columns of memory locations such that memory locations within a column of memory locations are accessed in turn before a next column of memory locations is selected for access;
 - (viii) read data from, write specified data to and read data from a sequence of memory locations within a memory arranged in rows and columns of memory locations such that memory locations within a row of memory locations are accessed in turn before a next row of memory locations is selected for access;
 - (ix) read data from, write specified data to and read data from to a sequence of memory locations within a memory arranged in rows and columns of memory locations such that memory locations within a column of memory locations are accessed in turn before a next column of memory locations is selected for access;
 - (x) for a sequence of memory locations, repeatedly write a value to one or more bitlines within said memory and then read a complementary value stored within a memory location sharing said one or more bitlines; and
 - (xi) for a sequence of memory locations, repeatedly read a value from a memory location while interjecting opposing data writes;
 - (xii) a predetermined combination of memory test operations as defined in (i) to (xi) for go/nogo testing where manufacture's test methods do not have specific requirements; and

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- (xiii) creating false read data at specific points in order to validate fail detection.
- 25. A method as claimed in claim 18, wherein said at least one memory and said self-test controller formed together with a processor core on an integrated circuit.
- 26. A method as claimed in claim 18, wherein said at least one memory is one of a synthesized memory or a custom memory.
- 27. A method as claimed in claim 18, wherein values and timings of signals passed between said self-test controller and said at least one memory are adapted by an interface circuit disposed between said self-test controller and said at least one memory in order to accommodate differing value and timing properties of said at least one memory.
- 28. A method as claimed in claim 27, wherein said interface circuit maps a memory address value generated by said self-test controller to a logical address value to be input to said at least one memory.
- 29. A method as claimed in claim 18, wherein said self-test instruction specifies to which of a plurality of memories said self-test instruction applies.
 - 30. A method as claimed in claim 18, wherein said self-test instruction specifies in which of a plurality of different ways a detected memory error is to be reported by said self-test controller.
 - 31. A method as claimed in claim 27, wherein said interface circuit includes a result data register in which result data from testing said at least one memory may be captured and said self-test controller is responsive to a self-test instruction to read result data from said result data register.

- 32. A method as claimed in claim 18, wherein said self-test instruction specifies a size of said at least one memory to be tested.
- 5 33. A method as claimed in claim 18, wherein said self-test instruction is serially loaded into said self-test controller.
 - 34. A method as claimed in claim 18, wherein said at least one memory and said self-test controller are formed together on an integrated circuit having a plurality of external signal pins, said self-test controller having one or more external signal pins through which one or more self-test instructions may be applied to said self-test controller.